EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	53	ground same diode same pad same (n$1fet N$1type) same esd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/03 12:44
L2	2459	361/56.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/03 12:45
L3	106	(electrostatic near discharge esd) and pad and circuit and voltage and ground and diode and anode and transistor and gate and (nfet n$1type) and (pfet p$type)	US-PGPUB	OR	OFF	2006/04/03 12:47
L4	47	(electrostatic near discharge esd) and pad and circuit and voltage and ground and diode and anode and transistor and gate and (nfet n$1type) and (pfet p$type).clm.	US-PGPUB	OR	OFF	2006/04/03 12:48